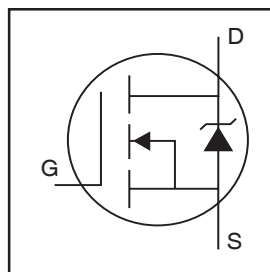


Features

- Advanced Process Technology
- Ultra Low On-Resistance
- 150°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}



$V_{DSS} = 55V$
$R_{DS(on)} = 57.5m\Omega$
$I_D = 5.1A$

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited) ⑦	5.1	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ⑦	4.1	
I_{DM}	Pulsed Drain Current ①	41	
$P_D @ T_A = 25^\circ C$	Power Dissipation ⑦	2.8	W
$P_D @ T_A = 25^\circ C$	Power Dissipation ⑧	1.0	
	Linear Derating Factor ⑦	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	13	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ⑥	32	
I_{AR}	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ⑦	—	45	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ⑧	—	120	

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.053	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	46.2	57.5	m Ω	$V_{GS} = 10V, I_D = 3.1A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	6.2	—	—	S	$V_{DS} = 25V, I_D = 3.1A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	9.1	14	nC	$I_D = 3.1A$
Q_{gs}	Gate-to-Source Charge	—	1.9	—		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	3.9	—		$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	7.8	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	21	—		$I_D = 3.1A$
$t_{d(off)}$	Turn-Off Delay Time	—	30	—		$R_G = 53\Omega$
t_f	Fall Time	—	23	—		$V_{GS} = 10V$ ③
C_{iss}	Input Capacitance	—	340	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	68	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	39	—		$f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	210	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	55	—		$V_{GS} = 0V, V_{DS} = 44V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	93	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 44V$ ④

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	5.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	41		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 3.1A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	15	23	ns	$T_J = 25^\circ\text{C}, I_F = 3.1A, V_{DD} = 28V$
Q_{rr}	Reverse Recovery Charge	—	9.8	15	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 2.8\text{mH}$
 $R_G = 25\Omega, I_{AS} = 3.1A, V_{GS} = 10V$.
Part not recommended for use above this value.
- ③ Pulse width $\leq 1.0\text{ms}$; duty cycle $\leq 2\%$.
- ④ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

- ⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑥ This value determined from sample failure population. 100% tested to this value in production.
- ⑦ When mounted on 1 inch square copper board.
- ⑧ When mounted on FR-4 board using minimum recommended footprint.

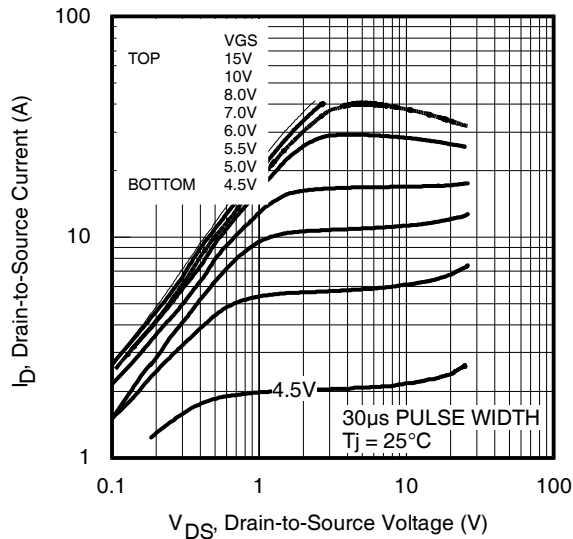


Fig 1. Typical Output Characteristics

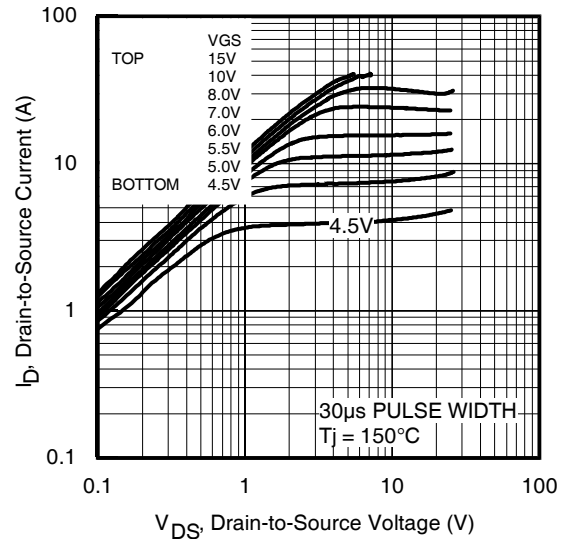


Fig 2. Typical Output Characteristics

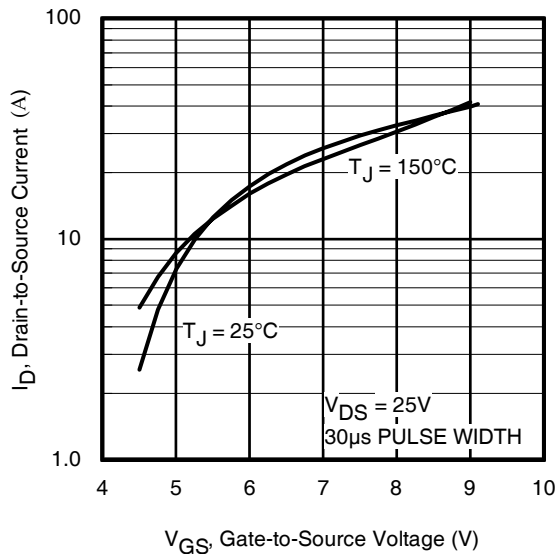


Fig 3. Typical Transfer Characteristics

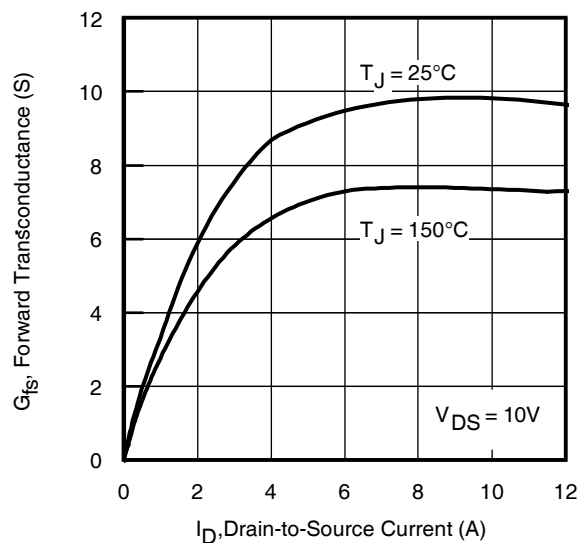
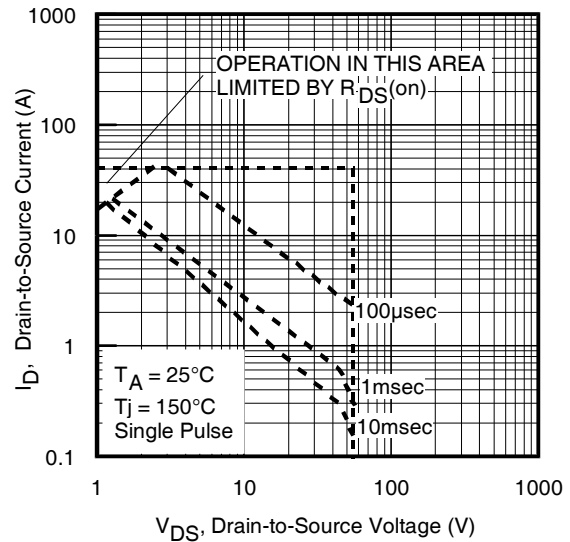
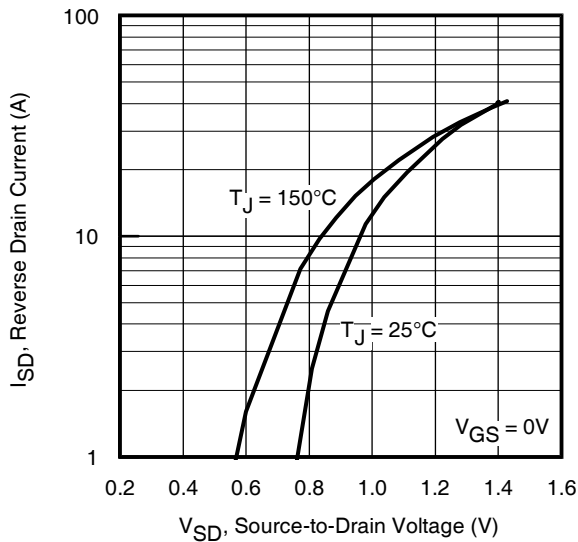
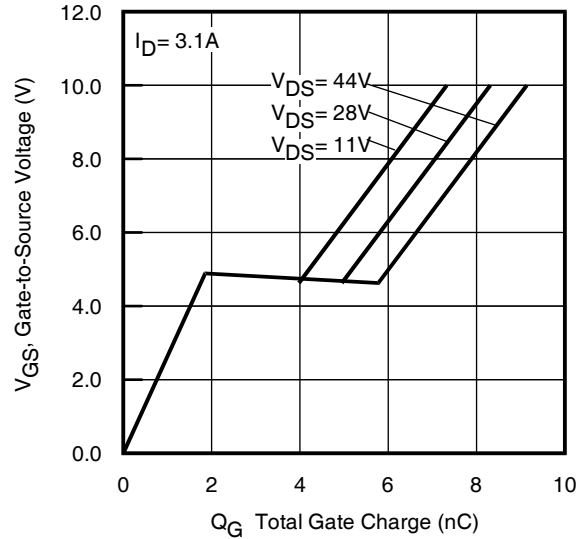
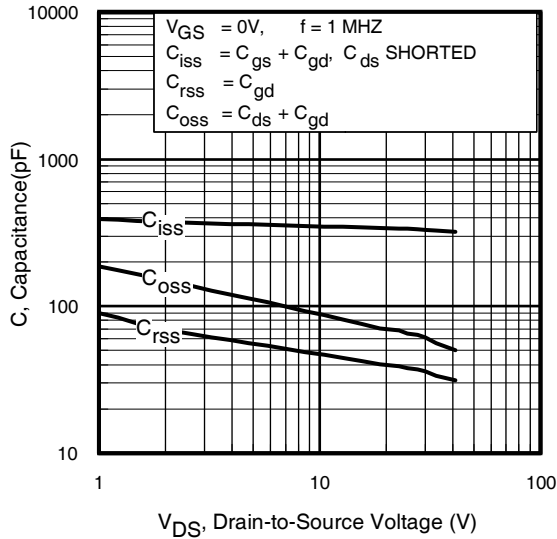


Fig 4. Typical Forward Transconductance vs. Drain Current



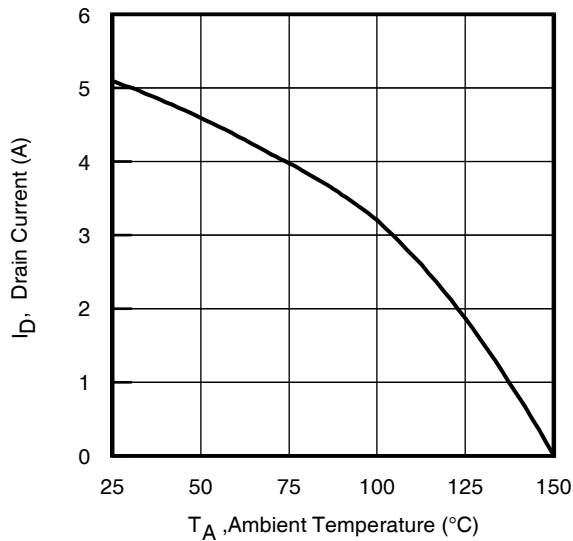


Fig 9. Maximum Drain Current vs. Ambient Temperature

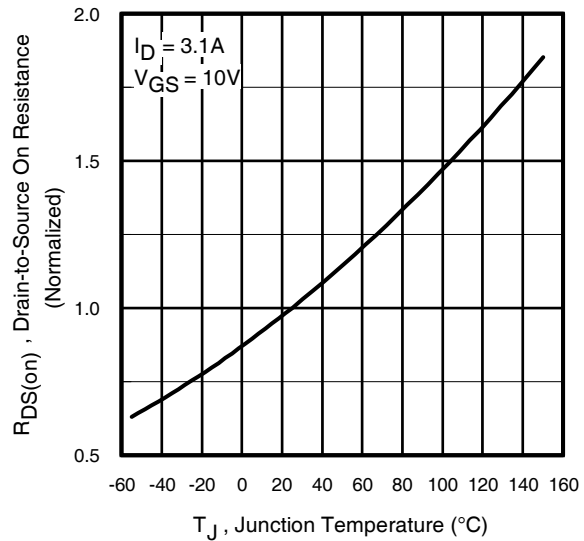


Fig 10. Normalized On-Resistance vs. Temperature

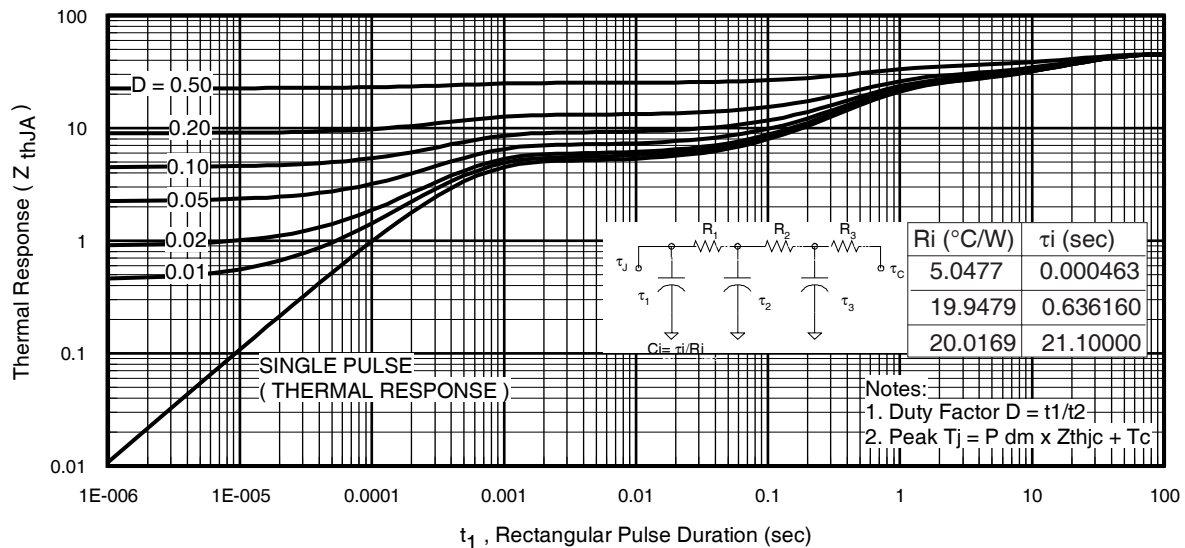


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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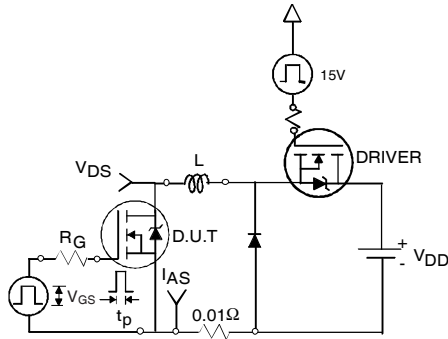


Fig 12a. Unclamped Inductive Test Circuit

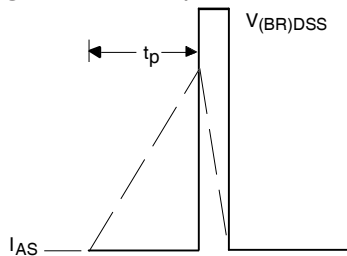


Fig 12b. Unclamped Inductive Waveforms

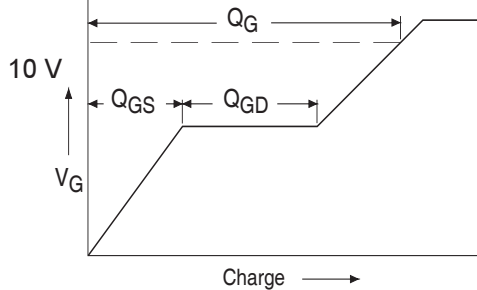


Fig 13a. Basic Gate Charge Waveform

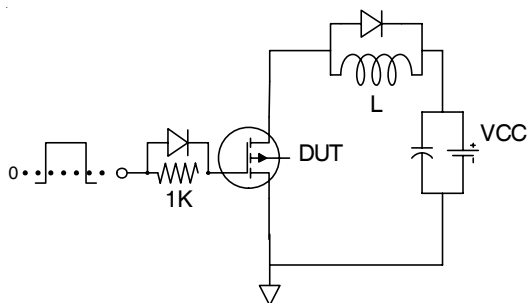


Fig 13b. Gate Charge Test Circuit

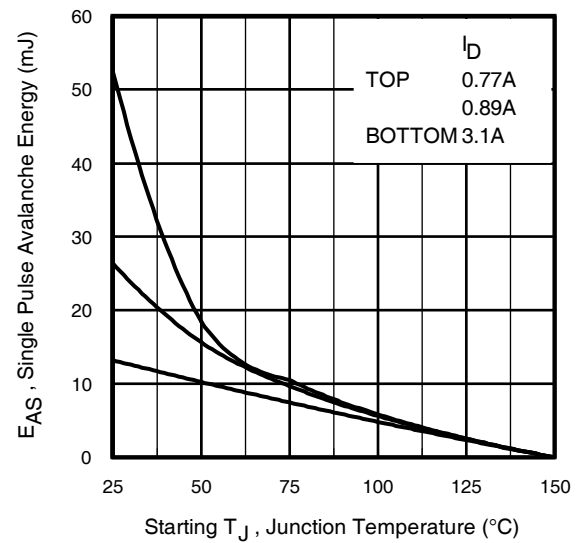


Fig 12c. Maximum Avalanche Energy vs. Drain Current

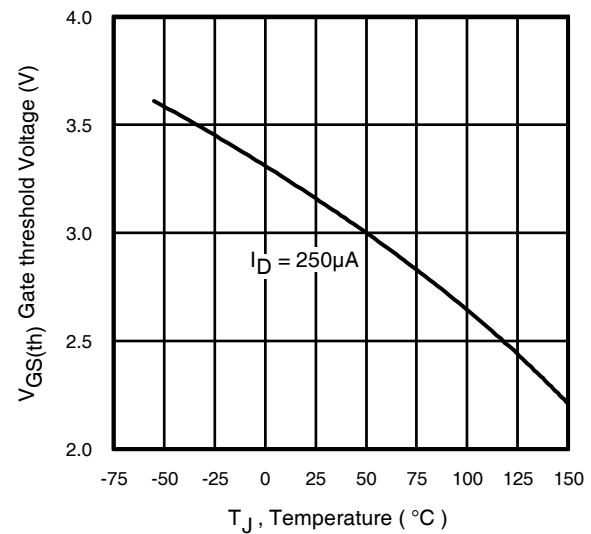


Fig 14. Threshold Voltage vs. Temperature

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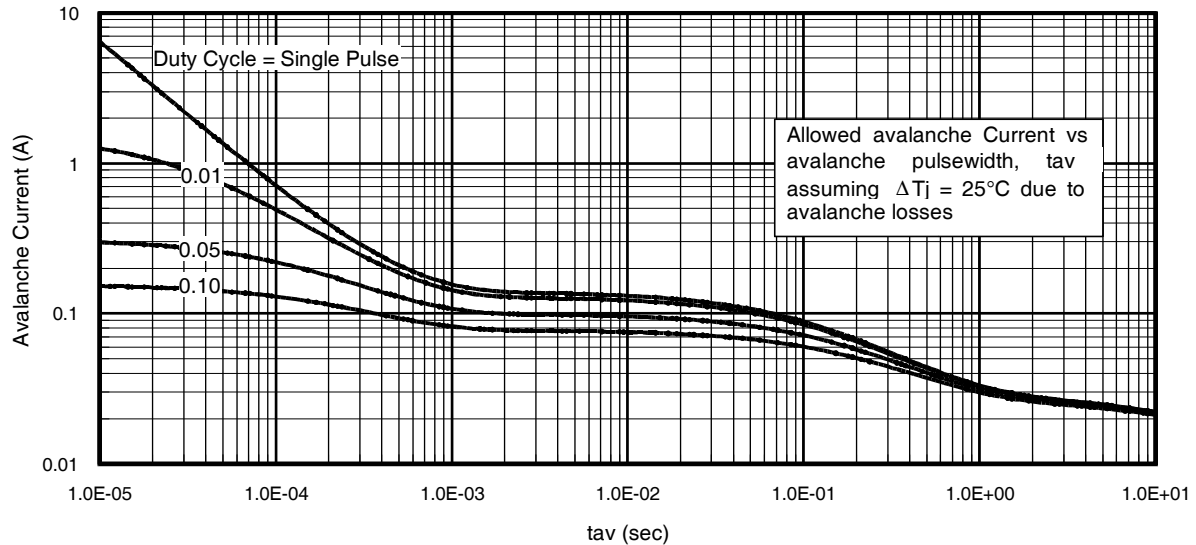


Fig 15. Typical Avalanche Current vs. Pulsewidth

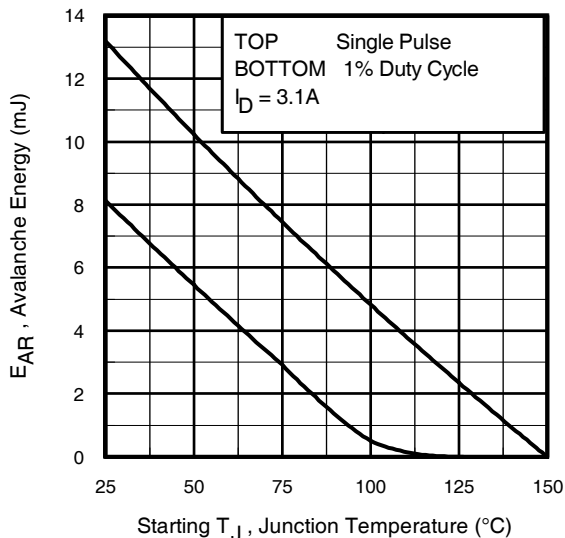


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

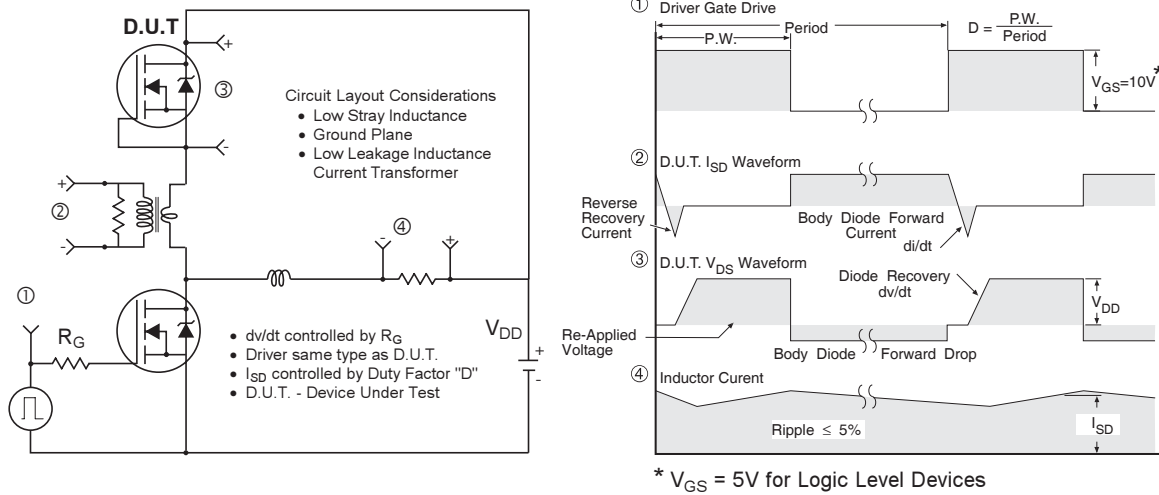


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

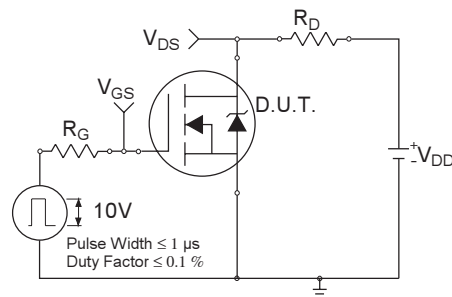


Fig 18a. Switching Time Test Circuit

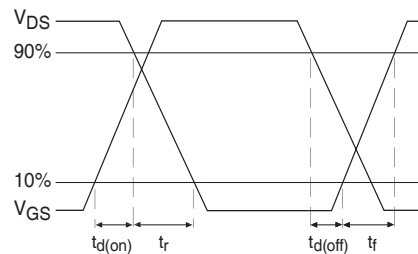
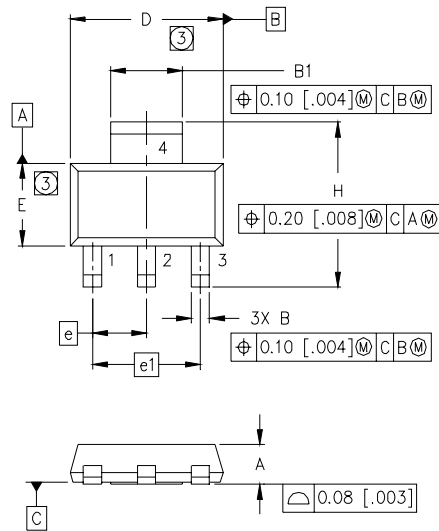
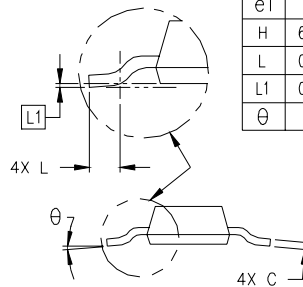


Fig 18b. Switching Time Waveforms

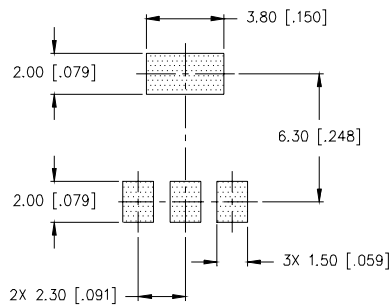
SOT-223 (TO-261AA) Package Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.55	1.80	.061	.071
B	0.65	0.85	.026	.033
B1	2.95	3.15	.116	.124
C	0.25	0.35	.010	.014
D	6.30	6.70	.248	.264
E	3.30	3.70	.130	.146
e	2.30	BSC	.0905	BSC
e1	4.60	BSC	.181	BSC
H	6.71	7.29	.264	.287
L	0.91	—	.036	—
L1	0.061	BSC	.0024	BSC
θ	—	10°	—	10°



MINIMUM RECOMMENDED FOOTPRINT



LEAD ASSIGNMENTS

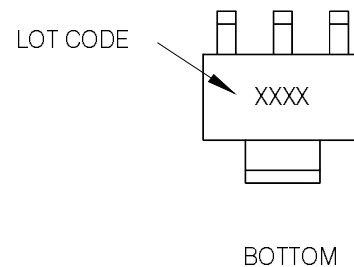
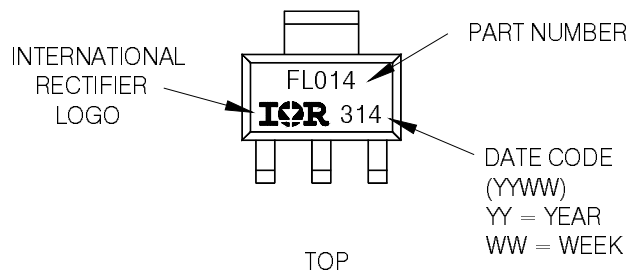
- 1 = GATE
- 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS DO NOT INCLUDE MOLD FLASH.
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

SOT-223 (TO-261AA) Part Marking Information

EXAMPLE: THIS IS AN IRFL014



SOT-223 (TO-261AA) Tape & Reel Information

Technical drawing of a mold cavity with dimensions in mm and inches. The drawing includes a top view, a side view, and a cross-section view. The top view shows a rectangular cavity with a central rectangular feature. The side view shows the profile of the cavity with a central rectangular feature. The cross-section view shows the internal structure of the cavity. Dimensions are provided in mm and inches.

Dimensions (mm) and (inches):

- Top View:
 - Overall Width: 12.10 (.475)
 - Overall Height: 11.90 (.469)
 - Central Feature Width: 4.10 (.161)
 - Central Feature Height: 3.90 (.154)
 - Left Side Width: 2.05 (.080)
 - Left Side Height: 1.95 (.077)
 - Right Side Width: 1.85 (.072)
 - Right Side Height: 1.65 (.065)
 - Central Feature Width: 7.55 (.297)
 - Central Feature Height: 7.45 (.294)
 - Central Feature Width: 7.10 (.279)
 - Central Feature Height: 6.90 (.272)
 - Central Feature Width: 1.60 (.062)
 - Central Feature Height: 1.50 (.059) TYP.
- Side View:
 - Overall Width: 16.30 (.641)
 - Overall Height: 15.70 (.619)
 - Central Feature Width: 7.60 (.299)
 - Central Feature Height: 7.40 (.292)
 - Central Feature Width: 2.30 (.090)
 - Central Feature Height: 2.10 (.083)
- Cross-section View:
 - Overall Width: 0.35 (.013)
 - Overall Height: 0.25 (.010)

FEED DIRECTION

Technical drawing of a shaft assembly. The drawing shows a shaft with a diameter of 50.00 (1.969) MIN. The shaft is supported by bearings. The dimensions and tolerances are as follows:

- Top dimension: 15.40 (.607)
- Top dimension: 11.90 (.469)
- Top dimension: 14.40 (.566)
- Top dimension: 12.40 (.488)
- Bottom dimension: 18.40 (.724) MAX.

The drawing includes two circular features labeled (4) and (3).

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